



CHENMKO ENTERPRISE CO.,LTD

CHM0410JGP

SURFACE MOUNT

N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 100 Volts CURRENT 3.4 Ampere

Halogens free devices

APPLICATION

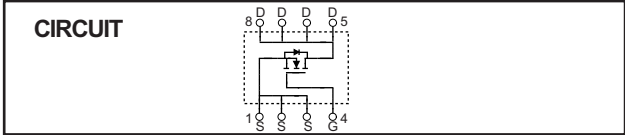
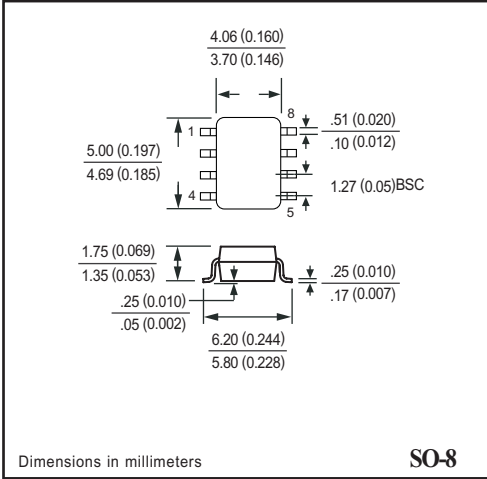
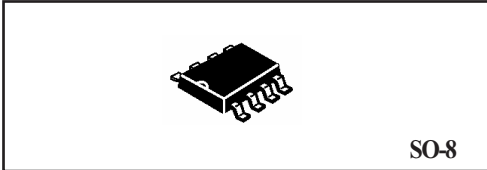
- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

- * Small flat package. (SO-8)
- * Super high dense cell design for extremely low $R_{DS(ON)}$.
- * High power and current handling capability.
- * Lead free product is acquired.

CONSTRUCTION

- * N-Channel Enhancement



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | CHM0410JGP | Units |
|-----------|------------------------------------|------------|------------------|
| V_{DSS} | Drain-Source Voltage | 100 | V |
| V_{GSS} | Gate-Source Voltage | ± 20 | V |
| I_D | Maximum Drain Current - Continuous | 3.4 | A |
| | - Pulsed (Note 3) | 13.6 | |
| P_D | Maximum Power Dissipation | 2500 | mW |
| T_J | Operating Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |

- Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$
 2. Pulse Test , Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
 3. Repetitive Rating , Pulse width limited by maximum junction temperature
 4. Guaranteed by design , not subject to production testing

Thermal characteristics

| | | | |
|-----------------|--|----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1) | 50 | $^\circ\text{C/W}$ |
|-----------------|--|----|--------------------|

ELECTRICAL CHARACTERISTIC (CHM0410JGP)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|--------|-----------|------------|-----|-----|-----|-------|
|--------|-----------|------------|-----|-----|-----|-------|

OFF CHARACTERISTICS

| | | | | | | |
|------------|---------------------------------|---|-----|--|------|---------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 100 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSSF} | Gate-Body Leakage | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | | | +100 | nA |
| I_{GSSR} | Gate-Body Leakage | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA |

ON CHARACTERISTICS (Note 2)

| | | | | | | |
|--------------|-----------------------------------|--|---|-----|-----|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 2 | | 4 | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 1.7\text{ A}$ | | 100 | 120 | $\text{m}\Omega$ |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|-----|--|----|
| C_{ISS} | Input Capacitance | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 540 | | pF |
| C_{OSS} | Output Capacitance | | | 100 | | |
| C_{RSS} | Reverse Transfer Capacitance | | | 22 | | |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|-----------|--------------------|--|--|-----|----|----|
| Q_g | Total Gate Charge | $V_{DS} = 80\text{ V}, I_D = 3.4\text{ A}$ $V_{GS} = 10\text{ V}$ | | 12 | 16 | nC |
| Q_{gs} | Gate-Source Charge | | | 2.5 | | |
| Q_{gd} | Gate-Drain Charge | | | 4.2 | | |
| t_{on} | Turn-On Time | $V_{DD} = 50\text{ V}$ $I_D = 3.4\text{ A}, V_{GS} = 10\text{ V}$ $R_{GEN} = 25\ \Omega$ | | 14 | 30 | nS |
| t_r | Rise Time | | | 3 | 7 | |
| t_{off} | Turn-Off Time | | | 38 | 80 | |
| t_f | Fall Time | | | 7.5 | 15 | |

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

| | | | | | | |
|----------|------------------------------------|--|--|--|-----|---|
| I_S | Drain-Source Diode Forward Current | (Note 1) | | | 3.4 | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $I_S = 3.4\text{ A}, V_{GS} = 0\text{ V}$ (Note 2) | | | 1.2 | V |

RATING CHARACTERISTIC CURVES (CHM0410JGP)

Typical Electrical Characteristics

Figure 1. Output Characteristics

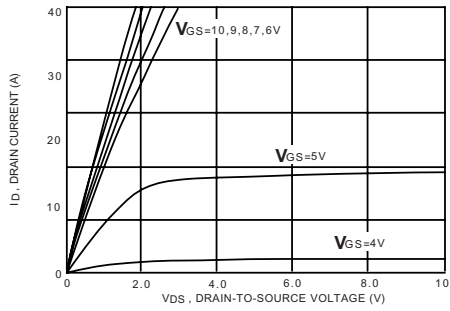


Figure 2. Transfer Characteristics

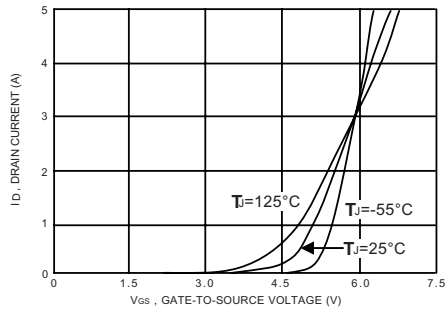


Figure 3. Gate Charge

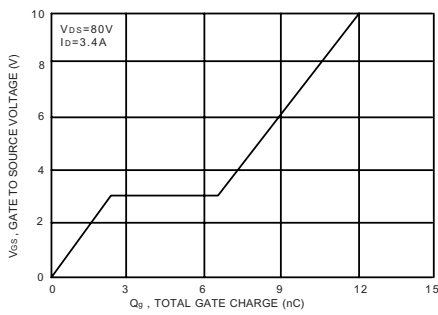


Figure 4. On-Resistance Variation with Temperature

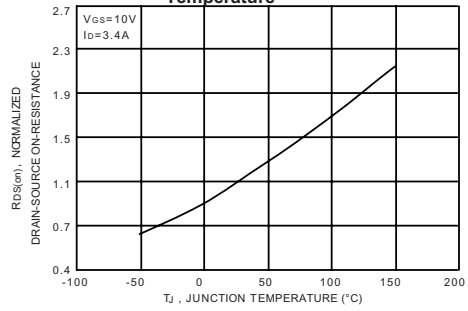


Figure 5. Gate Threshold Variation with Temperature

